



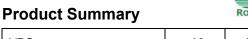
-30V P-Channel MOSFET

General Features

- $R_{DS(ON)}$ < 20m Ω @ VGS = -10V $R_{DS(ON)}$ < 33m Ω @ VGS = -4.5V
- High Power and Current Handing Capability
- Lead Free Product is Acquired
- Surface Mount Package

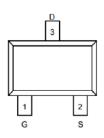
Applications

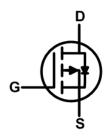
- PWM Applications
- Load Switch
- Power Management



VDS	-30	V
RDS(on),max.@ VGS=-10 V	20	mΩ
ID	-9	Α







P-channel

Absolute Maximum Ratings (T_C =25 $^{\circ}$ C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±12	V
	Continuous Drain Current	T _C = 25°C	-9	^
l _D		T _C = 100°C	-5	_ A
I _{DM}	Pulsed Drain Current note1		-15	А
PD	Power Dissipation	T _C = 25°C	1.8	W
Rejc	Thermal Resistance, Junction to Ambient		6.9	°C/W
TJ, TSTG	Operating and Storage Temperature Range		-55 to +150	$^{\circ}$ C



-30V P-Channel MOSFET

Electrical Characteristics (T_C=25 °C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Characteristic							
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D = -250µA	-30	-	-	V	
IDSS	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μΑ	
Igss	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA	
On Charac	cteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V	
Б	Static Drain-Source on-Resistance	V _{GS} =-10.V, I _D =-5 A	-	16	20	mΩ	
$R_{DS(on)}$		V _{GS} =-4.5V, I _D =-3.0A	-	23	33		
g FS	Forward Transconductance	V _{DS} =-5V, I _D = -5.0A	20	-	-	S	
Dynamic (Characteristics						
Ciss	Input Capacitance		-	1300	-	pF	
Coss	Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	-	240	-	pF	
Crss	Reverse Transfer Capacitance	f = 1.0MHz	-	95	-	pF	
Q_g	Total Gate Charge	V _{DS} = -15V, I _D = -5A,	-	20	50	nC	
Qgs	Gate-Source Charge	$V_{GS} = -1.0V$	-	4	-	nC	
Q _{gd}	Gate-Drain("Miller") Charge	763 1.00	-	6	-	nC	
Switching	Characteristics						
t _{d(on)}	Turn-on Delay Time		-	11	-	ns	
t_{r}	Turn-on Rise Time	$V_{DS} = -15V$, $I_{D} = -4A$,	-	18	-	ns	
t _{d(off)}	Turn-off Delay Time	R_{GEN} =2.5 Ω , V_{GS} =-1.0 V	-	30	-	ns	
tf	Turn-off Fall Time		-	10	-	ns	
Drain-Sou	rce Diode Characteristics and Maxin	num Ratings					
ls	Maximum Continuous Drain to Source Diode Forward Current		-	-	-7	Α	
Ism	Maximum Pulsed Drain to Source Diode Forward Current			-	-10	Α	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -5A	-	-	-1.2	٧	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

^{2.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%



Typical Performance Characteristics

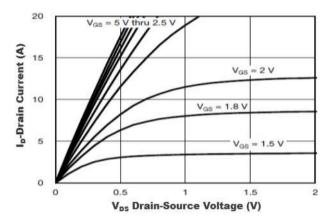


Figure 1. Output Characteristics

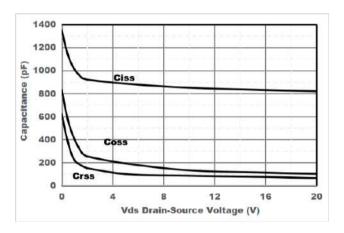


Figure 3. Capacitance Characteristics

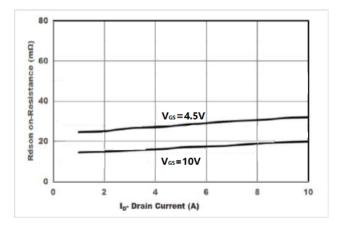


Figure 5. Drain-Source on Resistance

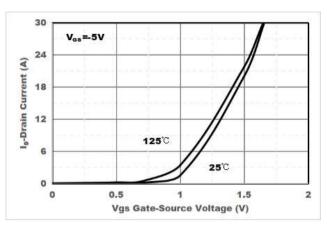


Figure 2. Transfer Characteristics

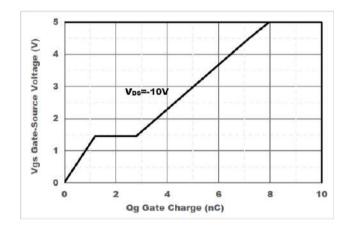


Figure 4. Gate Charge

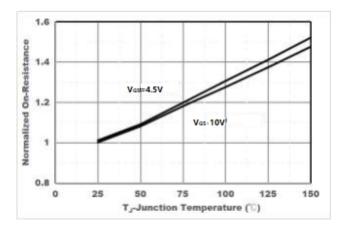


Figure 6. Drain-Source on Resistance



-30V P-Channel MOSFET

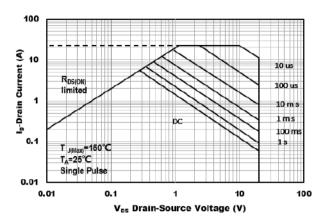


Figure 7. Safe Operation Area

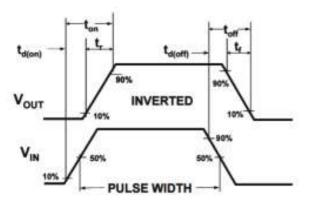


Figure8. Switching wave



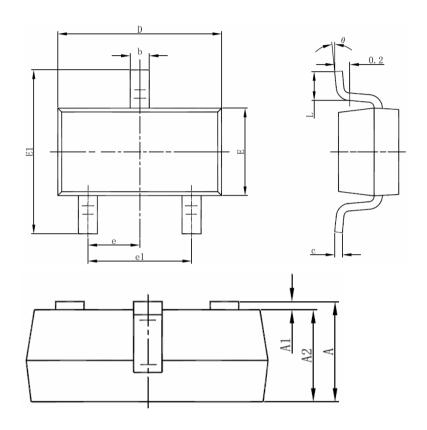
Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM30P09ZB-R	30P09	SOT23-3	Tape&Reel	3000/Reel
ASDM30P09ZB-R	3007	SOT23-3	Tape&Reel	3000/Reel

PACKAGE	MARKING
SOT23-3	30P09 ☐ Lot Number
SOT23-3	3007 Lot Number



SOT-23-3L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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ASDM30P09ZB

-30V P-Channel MOSFET

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TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1 IPS60R1K0PFD7SAKMA1

IPS60R360PFD7SAKMA1 IPS60R600PFD7SAKMA1